

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013 PHONE: (215) 631-9840 FAX: (215) 631-9855

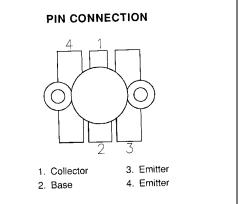
RF & MICROWAVE TRANSISTORS UHF MOBILE APPLICATIONS

Features

- 470 MHz
- 12.5 VOLTS
- **P**out = 25.0 WATTS
- $G_P = 6.2 \text{ dB MINIMUM}$
- COMMON EMITTER CONFIGURATION



The MS1429-03 is an epitaxial silicon NPN planar transistor designed for broadband applications in the 450-512MHz land Mobile radio band. This device utilizes diffused emitter resistors to withstand 20:1 VSWR at rated operating conditions.



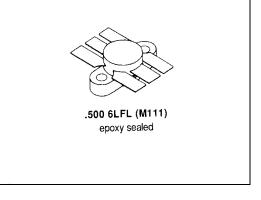
ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage	36	V	
V _{CEO}	Collector-Emitter Voltage	18	v	
V _{CES}	Collector-Emitter Voltage	36	V	
V _{EBO}	Emitter-Base Voltage	4.0	V	
lc	Collector Current	7.5	W	
P _{tot}	Total Power Dissipation	70.0	Α	
TJ	Junction Temperature	+200	°C	
T _{STG}	Storage Temperature	-65 to +150	°C	

THERMAL DATA

R _{TH(J-C)} Thermal Resistance Junction-case	2.5	°C/W
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ELECTRICAL SPECIFICATIONS (Tcase = 25°C) STATIC

Symbol	Test Conditions		Value		l Init	
		Min.	Тур.	Max.	Unit	
BV _{CES}	I _c = 10 mA	V _{BE} = 0 mA	36			V
BV _{CEO}	I _c = 50 mA	$I_B = 0 V$	18			v
BV _{EBO}	l _c = 5 mA	I _c = 0 mA	4.0			v
I _{CBO}	V _{CB} = 15 V	I _E = 0 mA			5	mA
h _{FE}	$V_{CE} = 5.0 V$	I _C = 1.0 A	10.0			

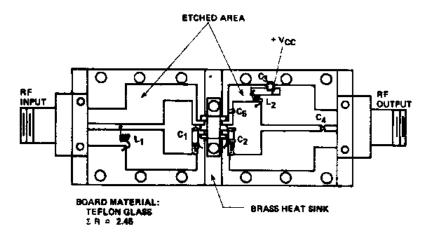
DYNAMIC

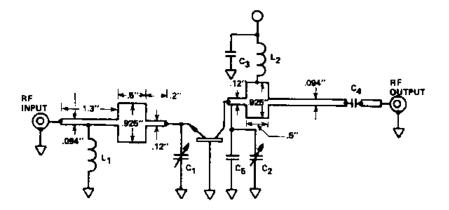
Symbol	Test Conditions	Value		Unit		
		Test conditions	Min.	Тур.	Max.	Unit
Ρουτ	f = 836 MHz	V _{CE} = 12.5V	25.0			W
G _P	f = 836 MHz	V _{CE} = 12.5V	5.5			dB
Сов	f = 1 MHz	V _{CB} = 12.5 V			75	рF



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TEST CIRCUIT





S88SD1421-06

COMPONENTS LIST C1, C2 .5 - 5.0pF Johanson E5851

L1, L2 4.5 TURNS # 22. .09" I.D.

C3 470pF, 100MIL SQ ATC C4 .001MF 50MIL SQ ATC 200A 102MC 50 C5 3.2pF 50MIL SQ ATC



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PACKAGE MECHANICAL DATA

